

Solar mono-crystalline PERC silicon cell

Mechanical data and design

Format	156.75mmx156.75mm±0.25mm
Thickness (Si)	190µm±20µm
Front (-)	Silicon oxide + blue silicon nitride compound
Back (+)	Passivated Emitter (AlOx and SiNx dual layer) rear contact

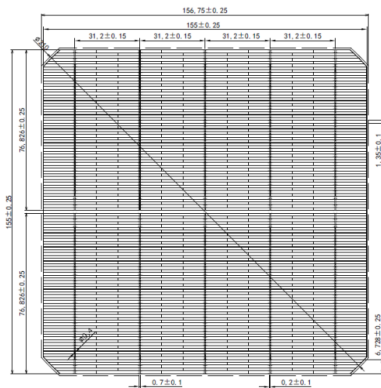
Temperature coefficients

TkVoltage	-0.32%/k
TkCurrent	+0.04%/k
TkPower	-0.42%/k

Efficiency	Isc(A)	Uoc(V)	Impp(A)	Umpp(V)	Pmpp(W)	FF(%)
22.30%-22.40%	9.829	0.6790	9.378	0.581	5.45	81.64
22.20%-22.30%	9.813	0.6770	9.368	0.579	5.42	81.64
22.10%-22.20%	9.798	0.6751	9.326	0.579	5.4	81.63
22.00%-22.10%	9.771	0.6739	9.300	0.578	5.37	81.63
21.90%-22.00%	9.742	0.6730	9.258	0.578	5.35	81.62
21.80%-21.90%	9.715	0.6720	9.232	0.577	5.33	81.59
21.70%-22.80%	9.675	0.6715	9.201	0.576	5.3	81.58
21.60%-21.70%	9.661	0.6702	9.186	0.575	5.28	81.55
21.50%-21.60%	9.657	0.6674	9.181	0.572	5.25	81.51
21.40%-21.50%	9.633	0.666	9.157	0.571	5.23	81.5
21.30%-21.40%	9.611	0.6657	9.149	0.569	5.2	81.33
21.20%-21.30%	9.601	0.6651	9.121	0.568	5.18	81.11

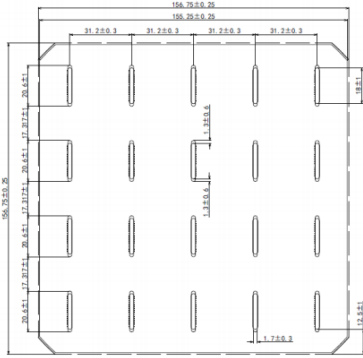
Date under standard testing conditions(STC):1000W/ m²,AM1.5,25°C

TZ Solar mono-crystalline silicon cell

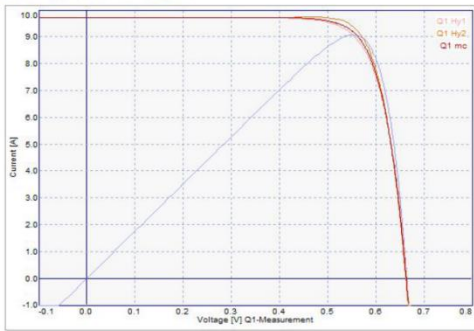


Solder Ability

Side	Peel strength
Front side average	>1.0N/mm
Back side average	>1.5N/mm



[Q1] Forward voltage with light



Light intensity dependance

Intensity W/m ²	V _{pm}	I _{pm}
1000	1	1
800	0.990	0.801
600	0.977	0.600
200	0.923	0.195

V_{pm}=maximum power voltage

I_{pm}= maximum power current